SLLS151D - DECEMBER 1988 - REVISED APRIL 2003

 Meet or Exceed the Requirements of SN65C1154 N PACKAGE TIA/EIA-232-F and ITU Recommendation V.28 SN75C1154 DW, N, OR NS PACKA (TOP VIEW) 							
 Very Low Power Consumption 5 mW Typ 	V _{DD} [1 20] V _{CC} 1RA [2 19] 1RY						
 Wide Driver Supply Voltage ±4.5 V to ±15 V 	1DY [] 3 18 [] 1DA 2RA [] 4 17 [] 2RY						
 Driver Output Slew Rate Limited to 30 V/µs Max 	2DY [5 16] 2DA 3RA [6 15] 3RY						
 Receiver Input Hysteresis 1000 mV Typ Push-Pull Receiver Outputs 	3DY [] 7 14 [] 3DA 4RA [] 8 13 [] 4RY						
 Push-Pull Receiver Outputs On-Chip Receiver 1-μs Noise Filter 	4DY [] 9 12 [] 4DA V _{SS} [] 10 11 [] GND						

description/ordering information

The SN65C1164 and SN75C1154 are low-power BiMOS devices containing four independent drivers and receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). These devices are designed to conform to TIA/EIA-232-F. The drivers and receivers of the SN65C1154 and SN75C1154 are similar to those of the SN75C188 quadruple driver and SN75C189A quadruple receiver, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/ μ s and the receivers have filters that reject input noise pulses of shorter than 1 μ s. Both these features eliminate the need for external components.

The SN65C1154 and SN75C1154 have been designed using low-power techniques in a BiMOS technology. In most applications, the receivers contained in these devices interface to single inputs of peripheral devices such as ACEs, UARTs, or microprocessors. By using sampling, such peripheral devices usually are insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN65C1154 and SN75C1154 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

TA	PACKAC	€‡	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	PDIP (N)	Tube of 20	SN65C1154N	SN65C1154N
PDIP (N)	PDIP (N)	Tube of 20	SN75C1154N	SN75C1154N
0°C to 70°C	SOIC (DW)	Tube of 25	SN75C1154DW	SN75C1154
0010700		Reel of 2500	SN75C1154DWR	311/301134
	SOP (NS)	Reel of 2000	SN75C1154NSR	SN75C1154

ORDERING INFORMATION

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

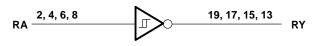


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logic diagram (positive logic)

Typical of Each Receiver

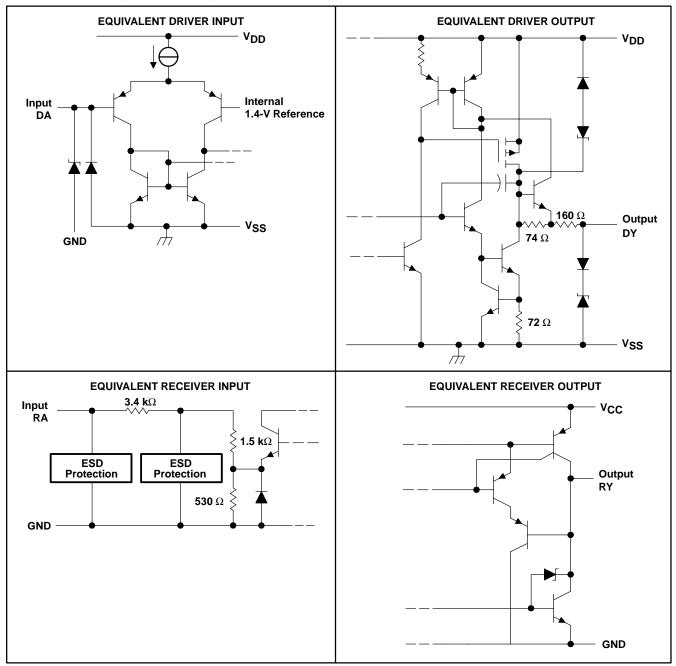


Typical of Each Driver





SLLS151D - DECEMBER 1988 - REVISED APRIL 2003



schematics of inputs and outputs

Resistor values shown are nominal.



SLLS151D - DECEMBER 1988 - REVISED APRIL 2003

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage: V _{DD} (see Note 1)	15 V
V _{SS}	
V _{CC}	
Input voltage range, V _I : Driver	\ldots V _{SS} to V _{DD}
Receiver	
Output voltage range, V _O :Driver	$(V_{SS} - 6 V)$ to $(V_{DD} + 6 V)$
Receiver	-0.3 V to (V _{CC} + 0.3 V)
Package thermal impedance, θ_{JA} (see Notes 2 and 3): DV	/ package 58°C/W
Ng	backage 69°C/W
NŠ	package 60°C/W
Operating virtual junction temperature, T _J	150°C
Storage temperature range, T _{stg}	
Lead temperature 1,6 mm (1/16 inch) from case for 10 sec	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage s are with respect to the network GND terminal.

- 2. Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions

			MIN	NOM	MAX	UNIT
V _{DD}	Supply voltage		4.5	12	15	V
VSS	/SS Supply voltage				-15	V
VCC	Supply voltage		4.5	5	6	V
VI	Input voltage	Driver	V _{SS} + 2		V _{DD}	V
VI.	input voitage	Receiver			±25	v
VIH	High-level input voltage	Driver	2			V
VIL	Low-level input voltage	Driver			0.8	V
ЮН	High-level output current	Receiver			-1	mA
IOL	High-level output current	Receiver			3.2	mA
ТА	Operating free-air temperature	SN65C1154	-40		85	°C
		SN75C1154	0		70	0



SLLS151D - DECEMBER 1988 - REVISED APRIL 2003

DRIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%$ (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS		MIN	түр†	MAX	UNIT
Vou	High-level output voltage	V _{IL} = 0.8 V,	R _L = 3 kΩ,	V _{DD} = 5 V,	$V_{SS} = -5 V$	4	4.5		V
Vон	High-level output voltage	See Figure 1	_	V _{DD} = 12 V,	$V_{SS} = -12 V$	10	10.8		v
Vei	Low-level output voltage	$V_{IH} = 2 V$, $R_L = 3 k\Omega$,		V _{DD} = 5 V,	$V_{SS} = -5 V$		-4.4	-4	V
VOL	(see Note 4)	See Figure 1		V _{DD} = 12 V,	$V_{SS} = -12 V$		-10.7	-10	v
IН	High-level input current	V _I = 5 V,	See Figure 2					1	μA
۱ _{IL}	Low-level input current	$V_{I} = 0,$	See Figure 2					-1	μA
IOS(H)	High-level short-circuit output current‡	V _I = 0.8 V,	$V_{O} = 0 \text{ or } V_{SS},$	See Figure 1		-7.5	-12	-19.5	mA
IOS(L)	Low-level short-circuit output current [‡]	V _I = 2 V,	$V_O = 0 \text{ or } V_{DD},$	See Figure 1		7.5	12	19.5	mA
	Supply ourrant from Van	No load,		V _{DD} = 5 V,	$V_{SS} = -5 V$		115	250	
IDD	Supply current from VDD	All inputs at 2 \	/ or 0.8 V	V _{DD} = 12 V,	$V_{SS} = -12 V$		115	250	μA
	Supply ourropt from Vac	No load,		V _{DD} = 5 V,	$V_{SS} = -5 V$		-115	-250	
ISS	Supply current from V_{SS}	All inputs at 2 V or 0.8		V _{DD} = 12 V,	$V_{SS} = -12 V$		-115	-250	μA
r _o	Output resistance	V _{DD} = V _{SS} = V	$V_{\rm CC} = 0$, $V_{\rm O} = -2$	2 V to 2 V,	See Note 5	300	400		Ω

[†] All typical values are at $T_A = 25^{\circ}C$.

[‡] Not more than one output should be shorted at one time.

NOTES: 4. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only.

5. Test conditions are those specified by TIA/EIA-232-F.

switching characteristics, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V \pm 10%, T_A = 25°C (see Figure 3)

					•	-	•
	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
^t PLH	Propagation delay time, low- to high-level output§	$R_L = 3 \text{ to } 7 \text{ k}\Omega,$	CL = 15 pF		1.2	3	μs
^t PHL	Propagation delay time, high- to low-level output§	$R_L = 3 \text{ to } 7 \text{ k}\Omega,$	CL = 15 pF		2.5	3.5	μs
^t TLH	Transition time, low- to high-level $\operatorname{output} \P$	$R_L = 3 \text{ to } 7 \text{ k}\Omega,$	CL = 15 pF	0.53	2	3.2	μs
^t THL	Transition time, high- to low-level $\operatorname{output} \P$	$R_L = 3 \text{ to } 7 \text{ k}\Omega,$	CL = 15 pF	0.53	2	3.2	μs
^t TLH	Transition time, low- to high-level output [#]	$R_L = 3 \text{ to } 7 \text{ k}\Omega$,	CL = 2500 pF		1	2	μs
^t THL	Transition time, high- to low-level output [#]	$R_L = 3 \text{ to } 7 \text{ k}\Omega$,	CL = 2500 pF		1	2	μs
SR	Output slew rate	$R_L = 3 \text{ to } 7 \text{ k}\Omega$,	CL = 15 pF	4	10	30	V/µs

§ tPHL and tPLH include the additional time due to on-chip slew rate control and are measured at the 50% points.

¶ Measured between 10% and 90% points of output waveform

[#] Measured between 3 V and –3 V points of output waveform (TIA/EIA-232-F conditions) with all unused inputs tied either high or low



SLLS151D - DECEMBER 1988 - REVISED APRIL 2003

RECEIVER SECTION

electrical characteristics over operating free-air temperature range, $V_{DD} = 12 V$, $V_{SS} = -12 V$, V_{CC} = 5 V \pm 10% (unless otherwise noted)

	PARAMETER	TEST CON	DITIONS	MIN	TYP†	MAX	UNIT
V _{IT+}	Positive-going input threshold voltage	See Figure 5		1.7	2.1	2.55	V
V _{IT} _	Negative-going input threshold voltage	See Figure 5		0.65	1	1.25	V
V _{hys}	Input hysteresis voltage (V _{IT+} – V _{IT–})			600	1000		mV
		$V_{I} = 0.75 V$, $I_{OH} = -20 \mu A$,	See Figure 5 and Note 6	3.5			
Vari			V _{CC} = 4.5 V	2.8	4.4		V
VOH	High-level output voltage	V _I = 0.75 V, I _{OH} = −1 mA, See Figure 5	V _{CC} = 5 V	3.8	4.9		v
		V _{CC} = 5.5 V	4.3	5.4			
VOL	Low-level output voltage	VI = 3 V, IOL = 3.2 mA,	See Figure 5		0.17	0.4	V
	Ligh lovel input ourrest	Vj = 25 V		3.6	4.6	8.3	~
ін	High-level input current	V _I = 3 V		0.43	0.55	1	mA
L.	Low lovel input ourrest	V _I = -25 V		-3.6	-5	-8.3	mA
۱L	Low-level input current	V _I = -3 V		-0.43	-0.55	-1	mA
IOS(H)	Short-circuit output at high level	$V_{I} = 0.75 V, V_{O} = 0,$	See Figure 4		-8	-15	mA
IOS(L)	Short-circuit output at low level	$V_I=V_{CC},\qquad V_O=V_{CC},$	See Figure 4		13	25	mA
laa		No load,	$V_{DD} = 5 V$, $V_{SS} = -5 V$		400	600	
lcc	Supply current from V_{CC}	All inputs at 0 or 5 V	$V_{DD} = 12 \text{ V}, V_{SS} = -12 \text{ V}$		400	600	μA

[†] All typical values are at $T_A = 25^{\circ}C$. NOTE 6: If the inputs are left unconnected, the receiver interprets this as an input low and the receiver outputs will remain in the high state.

switching characteristics, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V \pm 10%, T_A = 25°C

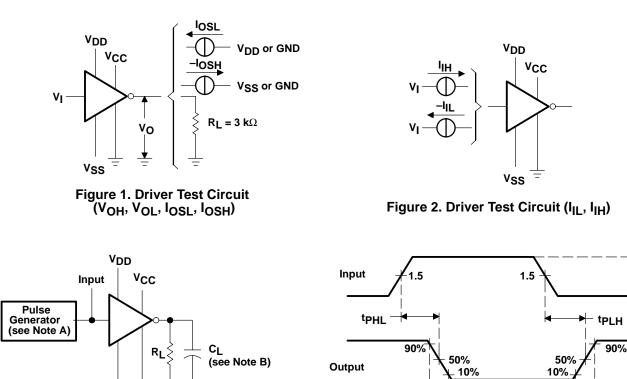
	PARAMETER	T	EST CONDITIO	MIN	TYP	MAX	UNIT	
^t PLH	Propagation delay time, low- to high-level output	C _L = 50 pF,	$R_L = 5 k\Omega$,	See Figure 6		3	4	μs
^t PHL	Propagation delay time, high- to low-level output	C _L = 50 pF,	$R_L = 5 k\Omega$,	See Figure 6		3	4	μs
^t TLH	Transition time, low- to high-level output	C _L = 50 pF,	$R_L = 5 k\Omega$,	See Figure 6		300	450	ns
^t THL	Transition time, high- to low-level output	C _L = 50 pF,	$R_L = 5 k\Omega$,	See Figure 6		100	300	ns
^t w(N)	Duration of longest pulse rejected as noise [‡]	C _L = 50 pF,	$R_L = 5 k\Omega$		1		4	μs

[‡] The receiver ignores any positive- or negative-going pulse that is less than the minimum value of t_{w(N)} and accepts any positive- or negative-going pulse greater than the maximum of $t_{W(N)}$.



SLLS151D - DECEMBER 1988 - REVISED APRIL 2003

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

Vss =

-

VOLTAGE WAVEFORMS

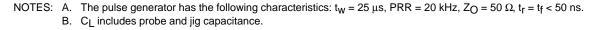


Figure 3. Driver Test Circuit and Voltage Waveforms

tTHL →

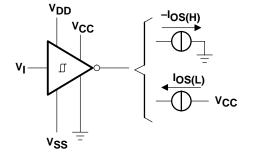
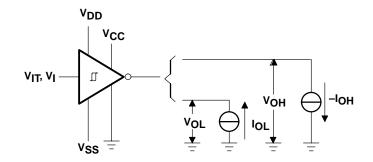


Figure 4. Receiver Test Circuit (IOSH, IOSL)







3 V

0 V

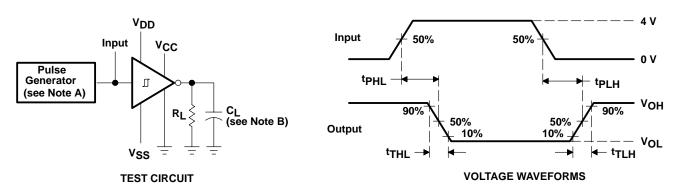
VOH

VOL

– ^tTLH

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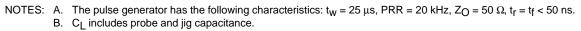


Figure 6. Receiver Test Circuit and Voltage Waveforms





PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material	(3)		(4/5)	
							(6)				
SN65C1154N	ACTIVE	PDIP	Ν	20	20	RoHS &	NIPDAU	N / A for Pkg Type	-40 to 85	SN65C1154N	Samples
						Non-Green					Samples
SN75C1154DW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1154	Samplas
											Samples
SN75C1154DWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1154	Samples
											Samples
SN75C1154N	ACTIVE	PDIP	Ν	20	20	RoHS &	NIPDAU	N / A for Pkg Type	0 to 70	SN75C1154N	Somplas
						Non-Green		0 71			Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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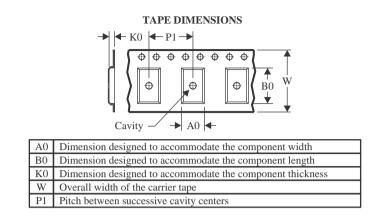


Texas

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal	

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN75C1154DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1



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PACKAGE MATERIALS INFORMATION

5-Dec-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN75C1154DWR	SOIC	DW	20	2000	350.0	350.0	43.0

TEXAS INSTRUMENTS

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5-Dec-2023

TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
SN65C1154N	N	PDIP	20	20	506	13.97	11230	4.32
SN75C1154DW	DW	SOIC	20	25	506.98	12.7	4826	6.6
SN75C1154N	N	PDIP	20	20	506	13.97	11230	4.32

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



DW0020A

EXAMPLE BOARD LAYOUT

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DW0020A

EXAMPLE STENCIL DESIGN

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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